AMENDMENTS TO THE CLAIMS

1. (Currently amended) A photovoltaic element comprising:

a transparent electrode comprising an ITO substrate and a metallic oxide layer or a derivative layer thereof, the ITO substrate being coated with the metallic oxide layer or derivative layer thereof, the metallic oxide layer or derivative layer being from 10nm to 100nm thick, the transparent electrode having a resistance of about 5 Ω/cm^2; and

a metallic oxide semiconductor layer contacting the metallic oxide layer or derivative layer thereof, the metallic oxide semiconductor layer comprising a light ~~sensitizer~~ sensitizing dye.

2. (Previously presented) The photovoltaic element according to claim 1, wherein the metallic oxide layer or derivative layer thereof includes at least one element among Ti, Cu, Zn, As, Sr, Nb, In, Sn and W.

3. (Previously presented) The photovoltaic element according to claim 1, wherein when the metallic oxide layer or derivative layer thereof is held for one hour in atmospheric air at 500°C, the rise of a resistance value is 10 Ω/cm^2 or lower.

4. (Previously presented) The photovoltaic element according to claim 1, wherein a light transmittance of the ITO substrate coated with the metallic oxide layer or derivative layer thereof, in the wavelength range from 400 nm to 900 nm, is 60% or higher.

5. (Canceled)

6. (Previously presented) The photovoltaic element of claim 1, wherein the metallic oxide semiconductor layer is sintered on the transparent electrode, and wherein the metallic oxide layer or derivative layer thereof prevents the resistance of the transparent electrode from rising more than 10 Ω/cm^2 when the metallic oxide semiconductor layer is sintered on the transparent electrode.

7. (Canceled)

8. (Previously presented) The photovoltaic element of claim 1, wherein the metallic oxide layer or derivative layer thereof comprises copper.

9. (Previously presented) The photovoltaic element of claim 1, wherein the metallic oxide layer or derivative layer thereof comprises tungsten.

10. (Previously presented) The photovoltaic element of claim 1, wherein the metallic oxide layer or derivative layer thereof comprises niobium.

11. (Previously presented) The photovoltaic element of claim 1, wherein the metallic oxide layer or derivative layer thereof comprises antimony.

12. (Previously presented) The photovoltaic element of claim 1, wherein the metallic oxide layer or derivative layer thereof comprises calcium.

13. (Previously presented) The photovoltaic element of claim 1, wherein the metallic oxide layer or derivative layer thereof comprises gallium.

14. (Currently Amended) The photovoltaic element of claim 1, wherein the metallic oxide layer or derivative layer thereof comprises ~~flourine-doped~~ fluorine-doped conductive glass.

15. (Previously presented) The photovoltaic element of claim 1, wherein the metallic oxide layer or derivative layer thereof comprises arsenic.

16. (Previously presented) The photovoltaic element of claim 1, wherein the metallic oxide layer or derivative layer thereof comprises indium.

17. (Previously presented) The photovoltaic element of claim 1, wherein the metallic oxide layer or derivative layer thereof comprises tin.